

#### NOT RECOMMENDED FOR NEW DESIGN **USE DMN2040U**

**DMN2041L** 

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

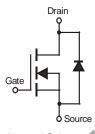
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

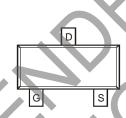
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)









Top View

Internal Schematic

Top View

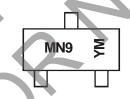
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041L-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



MN9 = Product Type Marking Code YM or \(\overline{Y}\)M = Date Code Marking for SAT Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

#### Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Υ		<u> </u>	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	6.4 4.5	А
Pulsed Drain Current (Note 6)	•		I <sub>DM</sub>	30	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.78	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C	R <sub>θJA</sub>	161	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

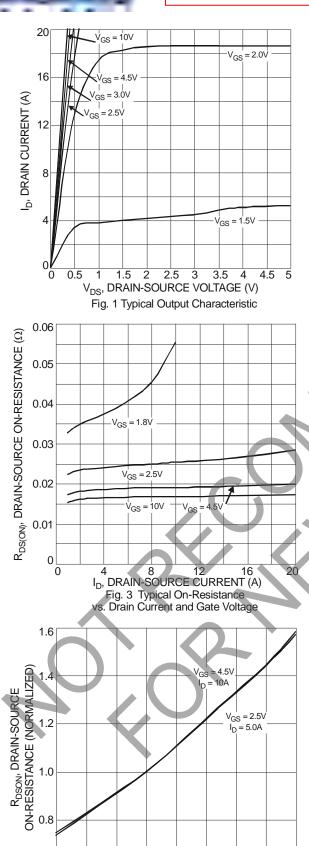
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	1		V	$V_{GS} = 0V$ , $I_D = 250\mu A$		
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_		1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$		
Gate-Source Leakage	IGSS	-	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5		1.2	V	$V_{DS}=V_{GS},I_D=250\mu A$		
Static Drain-Source On-Resistance	Paramo	7	20	28	mΩ	$V_{GS} = 4.5V, I_D = 6.0A$		
Static Dialif-Source Off-Resistance	R <sub>DS(ON)</sub>	1	26	41	11122	$V_{GS} = 2.5V, I_D = 5.2A$		
Forward Transfer Admittance	Y <sub>fs</sub>		6	_	S	$V_{DS} = 10V, I_D = 6A$		
Diode Forward Voltage	V <sub>SD</sub>		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.7A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C <sub>iss</sub>	_	550	_		.,		
Output Capacitance	Coss	_	88	_	pF	$V_{DS} = 10V$ , $V_{GS} = 0V$ , $f = 1.0MHz$		
Reverse Transfer Capacitance	C <sub>rss</sub>	1	81	_				
Gate Resistance	$R_g$	-	1.34	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$		
Total Gate Charge (10V)	Qg	_	15.6	_	nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$		
Total Gate Charge (4.5V)	Qg	_	7.2	_				
Gate-Source Charge	Qgs	_	1.0	_	nC	$V_{GS} = 4.5V$ , $V_{DS} = 10V$ , $I_{D} = 6A$		
Gate-Drain Charge	$Q_{gd}$	_	1.9	_				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.69	_				
Turn-On Rise Time	t <sub>R</sub>	_	13.19	_	ns	$V_{DD} = 10V, V_{GEN} = 4.5V,$ $R_{GEN} = 1\Omega, I_D = 6.7A$		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	22.10	_	110			
Turn-Off Fall Time	t <sub>F</sub>	_	6.43	_				

Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.



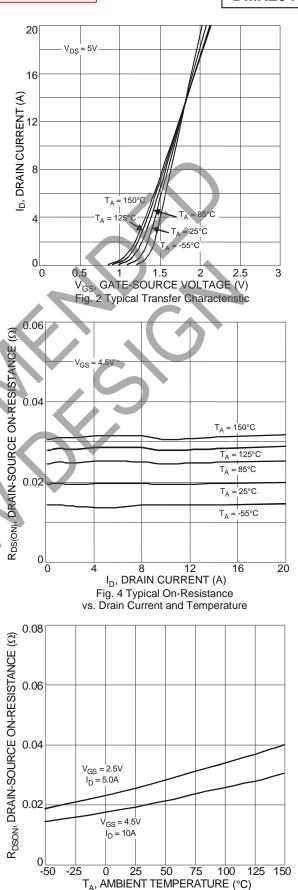


Fig. 6 On-Resistance Variation with Temperature

25

50

T<sub>A</sub>, AMBIENT TEMPERATURE (°C)

Fig. 5 On-Resistance Variation with Temperature

75

100 125 150

0.6\_

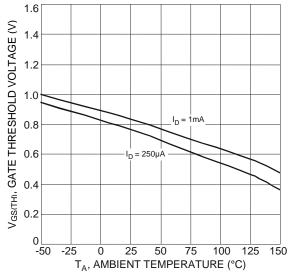
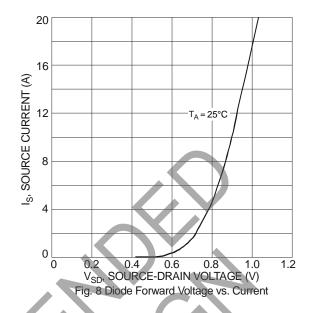
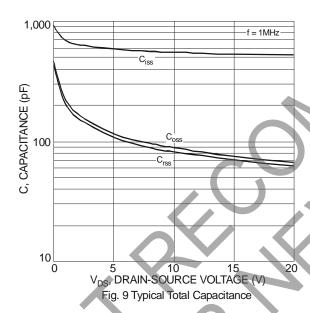


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





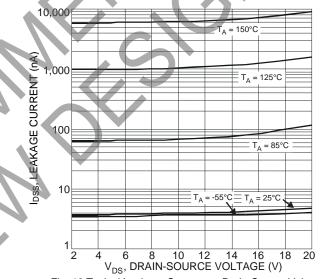


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

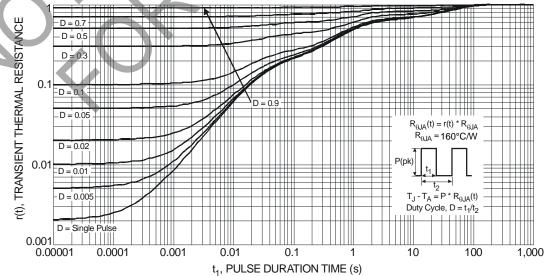


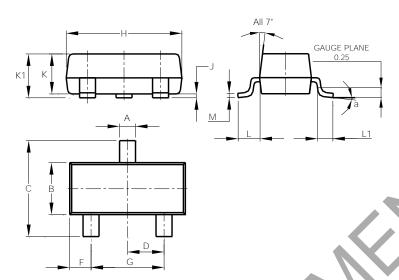
Fig. 11 Transient Thermal Response



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

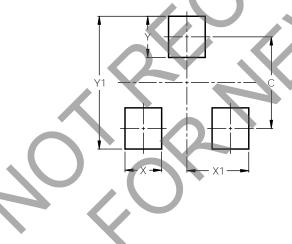


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	29



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**DMN2041L** 

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